

AMENDMENTS TO THE ABSTRACT

Please cancel the Abstract section of the specification and substitute the following:

A device including a silicon deposition mask provided with an electrode. The mask has a wiring connected to the electrode to supply a charge to a mask pattern section and an electrostatic chucking mechanism for attracting a subject for deposition using electrostatic attraction generated in the mask pattern section. The deposition mask controls the deposition of a material on the deposition subject with a predetermined pattern. An evaporation source evaporates the deposition material and a unit supplies the charge to the mask pattern section. At least the deposition mask and the evaporation source are placed in a vacuum chamber.